PROCESS CPD98V

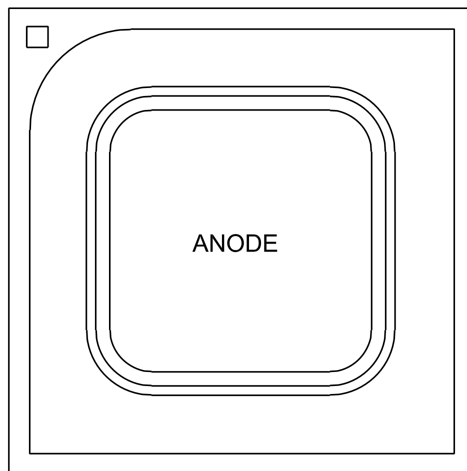
Schottky Diode

Silicon High Current Schottky Diode Chip

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	5.4 x 5.4 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

R0

GROSS DIE PER 5 INCH WAFER

141,234

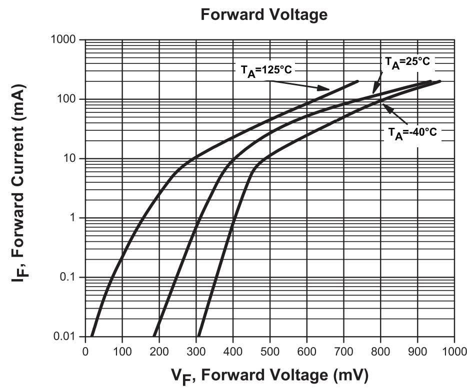
PRINCIPAL DEVICE TYPES

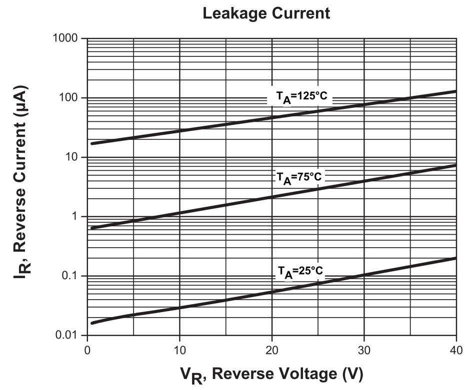
CMUSH2-4 Series

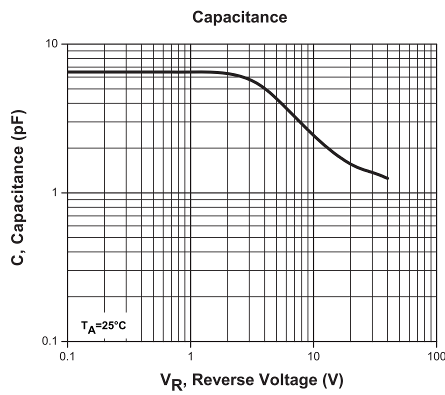
R2 (22-March 2010)

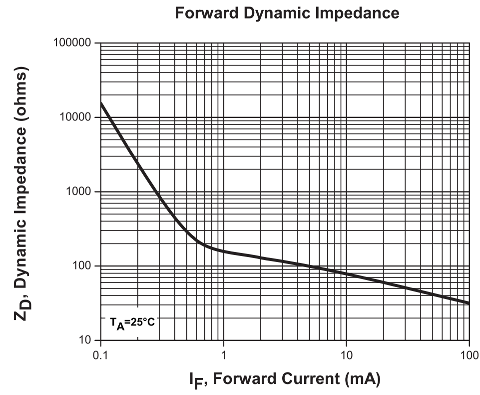
PROCESS CPD98V

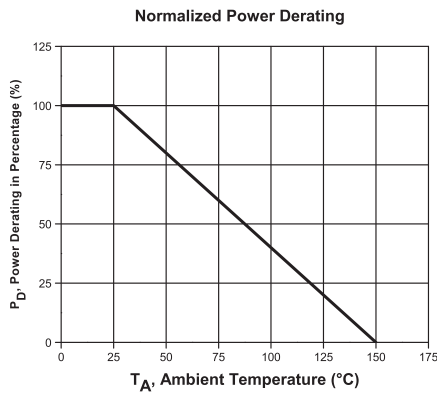
Typical Electrical Characteristics











R2 (22-March 2010)